
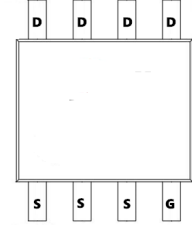


TMN3040S

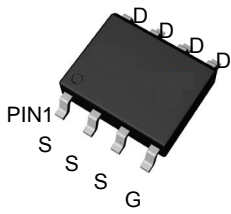
N-Channel Enhancement Mosfet

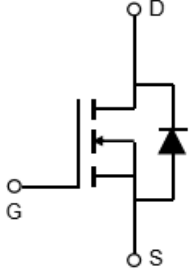
<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 30V$ $I_D = 40A$</p> <p>$R_{DS(ON)} = 6.5m\Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
--	---



PIN1

S:SOP-8L





Marking: 40N03

Absolute Maximum Ratings: ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_A=25^\circ C$	40	A
	Continuous Drain Current- $T_A=100^\circ C$	12	
I_{DM}	Drain Current-Pulsed ^{note1}	60	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	39	mJ
P_D	Power Dissipation	3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	41	$^\circ C/W$

TMN3040S
N-Channel Enhancement Mosfet
Electrical Characteristics: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=30V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1	1.5	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ^{note3}	$V_{GS}=10V, I_D=15A$	---	6.5	8	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	10	14	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	1110	---	pF
C_{oss}	Output Capacitance		---	180	---	
C_{rss}	Reverse Transfer Capacitance		---	150	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V, I_D=12A$ $R_{GEN}=3\ \Omega, V_{GS}=10V,$	---	15	---	ns
t_r	Rise Time		---	19	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	35	---	ns
t_f	Fall Time		---	21	---	ns
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V,$ $I_D=8A$	---	13.3	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	5	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=12A$	---	---	1.2	V
I_S	Continuous Drain to Source Diode Forward Current		---	---	40	A
I_{SM}	Pulsed Drain to Source Diode Forward Current		---	---	60	A
t_{rr}	Reverse Recovery Time	$I_F=12A, dI/dt=100A/\ \mu\text{s}$	---	14	---	ns
Q_{rr}	Reverse Recovery Charge		---	4.1	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^\circ\text{C}$, $V_{GS}=15V$, $R_G=25\ \Omega$, $L=0.5\text{mH}$, $I_{AS}=12.6A$
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

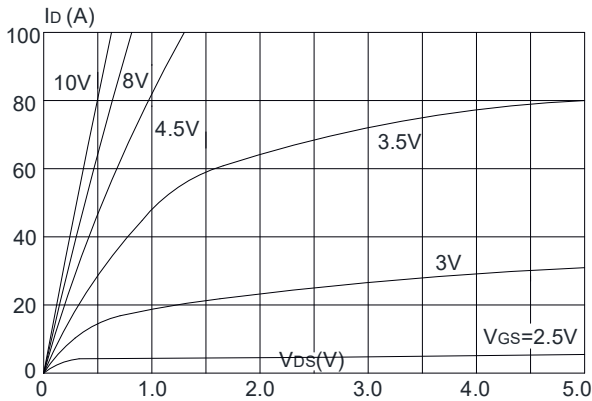


Figure 1: Output Characteristics

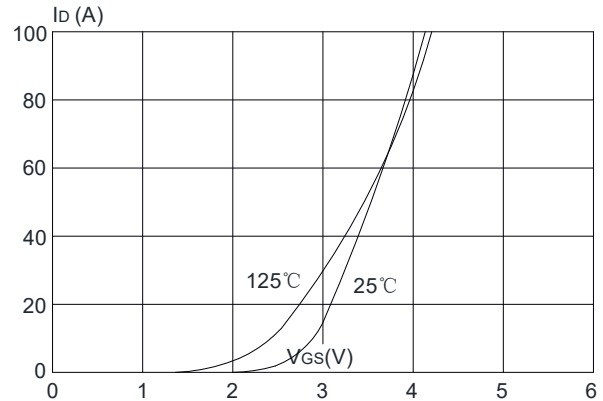


Figure 2: Typical Transfer Characteristics

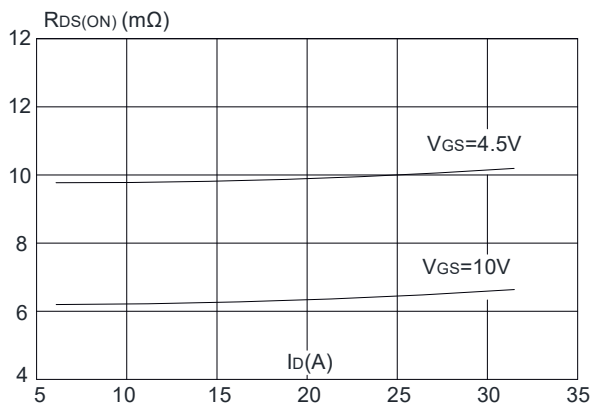


Figure 3: On-resistance vs. Drain Current

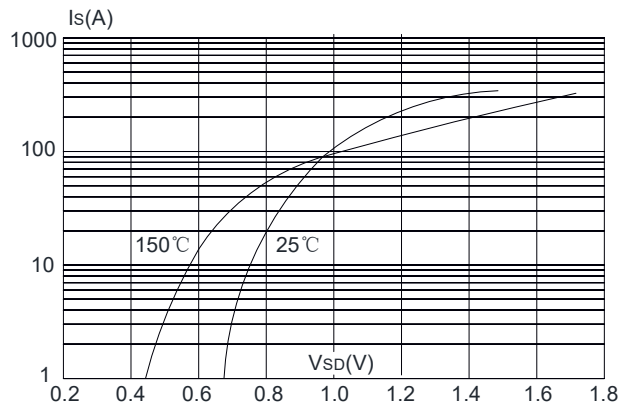


Figure 4: Body Diode Characteristics

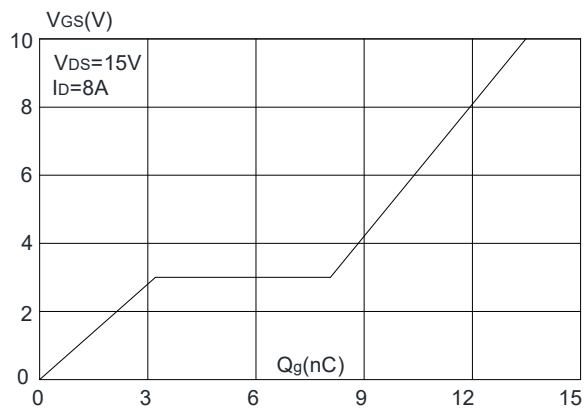


Figure 5: Gate Charge Characteristics

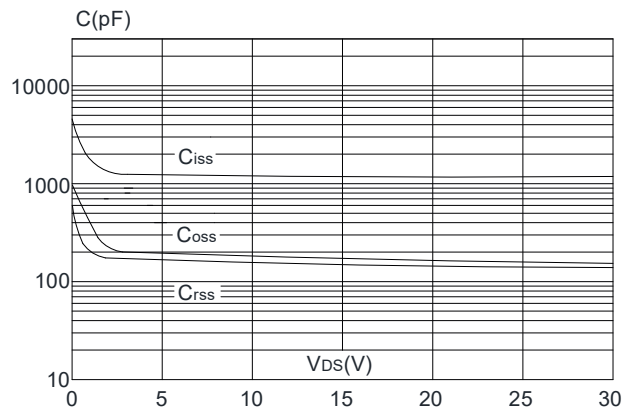


Figure 6: Capacitance Characteristics

N-Channel Enhancement Mosfet

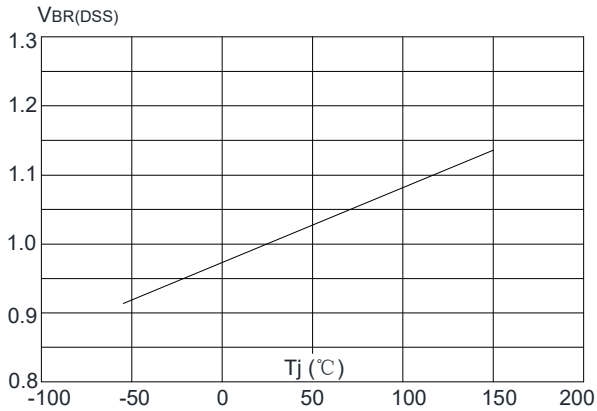


Figure 7: Normalized Breakdown Voltage vs.

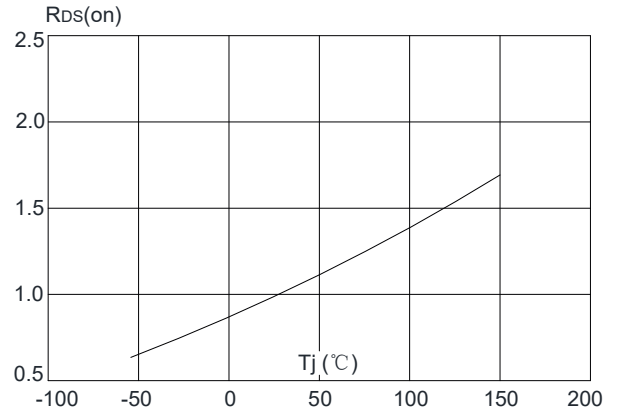


Figure 8: Normalized on Resistance vs. Junction Temperature

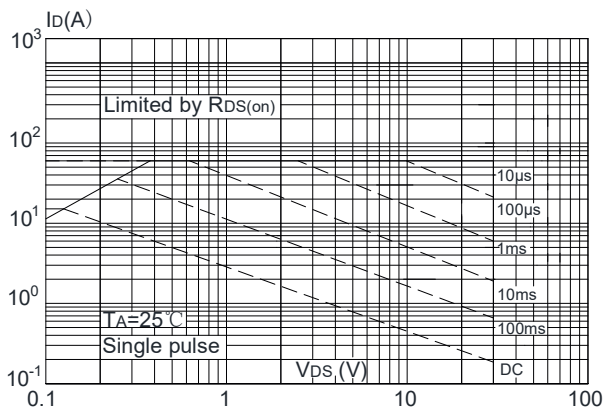


Figure 9: Maximum Safe Operating Area

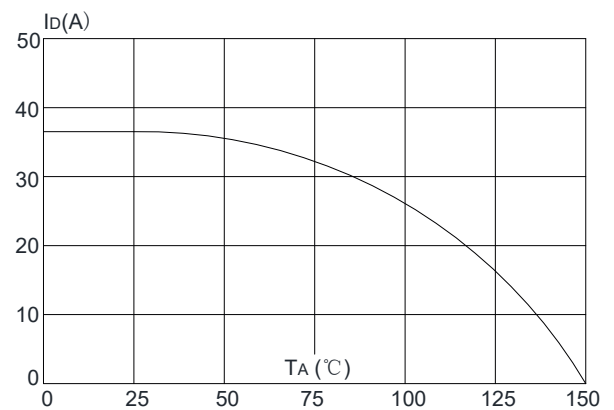


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

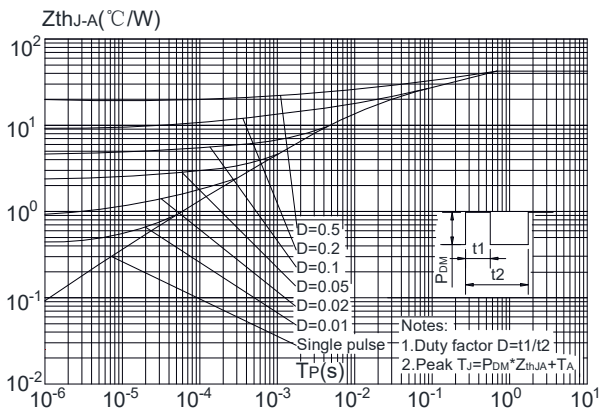
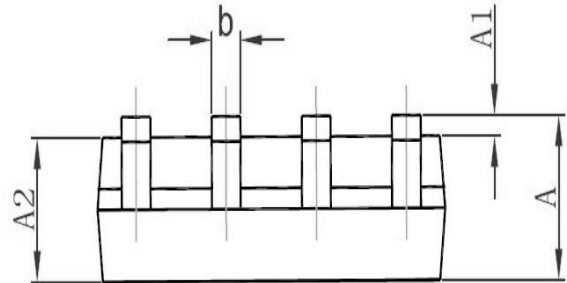
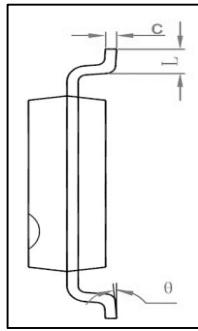
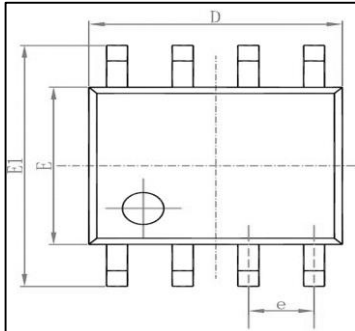
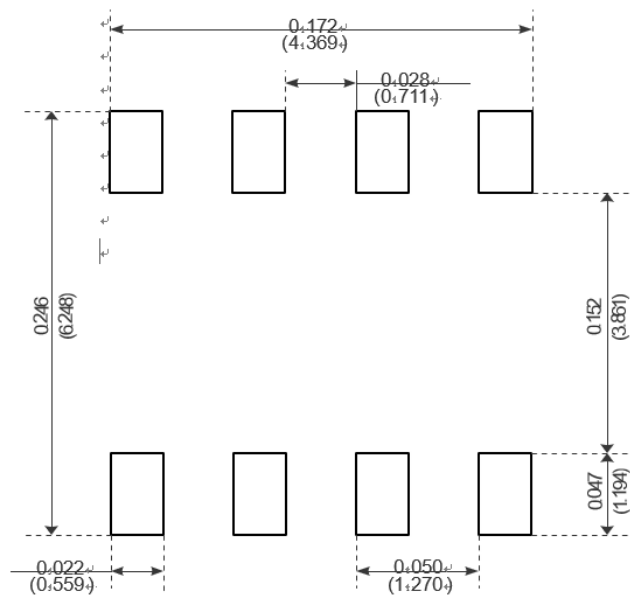


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Tritech-MOS](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#)
[BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#) [DMNH15H110SK3-13](#) [SLF10N65ABV2](#)
[BSO203SP](#) [BSO211P](#) [IPA60R230P6](#) [IPA60R460CE](#)